

## X-ray CoreLab Facilities at HZB

HyPerCell/HySPRINT Workshop, 12. 10. 2017

X-Ray CoreLab at HZB

- Methods and instruments
- Registration and booking

Susan Schorr Chair of the X-Ray CoreLab Steering Committee

## **Mission statement**

The **mission** of the X-Ray CoreLab is to use and to anchor the methods of lab-scale X-ray diffraction on an institutional and cross-cutting level in the HZB's strategy.

The X-ray CoreLab is supervised by a **Steering Committee** Susan Schorr, chair (EM-ASD) Christoph Genzel (EM-AME) Roel van de Krol (EE-IF) Bella Lake (EM-AQM)



#### The fundamental pillars of the X-ray corelab









## Investigation of polycrystalline samples

What is a polycrystalline material?

real space 15 5 -10 -15 -10 -15 -10 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 0 -5 -10 -5 0 -5 -10 -5 -5 -10 -5-1

## reciprocal space



3D periodic arrangement of atoms/ions/molecules

х

single crystal



four single crystals



## **Powder Diffraction (Bragg – Brentano – Geometry)**



## grazing incidence X-ray diffraction - GIXRD



sample: polycrystalline thin film

- parallel beam
- fixed incidence angle  $\omega$
- detector scan

## Information content of X-ray diffractograms

Features of diffraction methods: non-destructive phase selective □ information depth nm ... cm Line position and line shift: **Crystal structure** before sulphurization Intensity [a. u.] residual stress S<sub>2</sub> (220) /(204 202)/Cu (111) -Mo (110 Culn<sub>2</sub> ( Mo Ko Line width and line shape IS<sub>2</sub> (200 (211) □ micro strain, defects Mo KB Line intensity: 25 30 35 40 15 20 45 50 **Crystallographic texture** Energy [keV] reaction kinetics High energies >20 keV for: **Fluorescence lines:** □ ... High information depth element distribution □ ... XRF close to K-edges of many elements

## Instrumentation @ LMC

Bruker D8 Advance for analysis of thin films (I.) and powders (r.)



#### powder diffraction

- fast scans with LYNX Eye 1D detctor (~5-10 min)
- sample changer for high throughput
- *in situ* high temperature sample environment
- Bruker EVA and TOPAS for phase analysis
- ICDD-PDF-2 for phase analysis, upgrade to PDF-4 in progress
- web access to FIZ-ICSD

#### What can be done?

- qualitative phase analysis (search/match with database)
- quantitative phase analysis (Rietveld refinement with e.g. TOPAS)
- single peak fits: lattice parameter (rectangular crystal system) peak witdh (FWHM)
- structure refinement
  - LeBail refinement (lattice parameter) Rietveld refinement (all structural parameters)



## Anton Paar HTK 1200N High-Temperature Furnace-Chamber



#### Anton Paar HTK 1200N High-Temperature Furnace-Chamber

#### Specifications:

- $RT \le T \le 1200^{\circ}C$ ,  $dT/dt \approx 1K s^{-1}$
- oscillating sample holder for enhanced grain statistics
- motorized z-alignment stage to compensate for sample thicknesses and thermal expansion
- p<sub>min</sub> = 10<sup>-4</sup> mbar, air and inert gas atmosphere\*
- sample carriers for powders and thin films
  (Ø<sub>max</sub> = 20 mm)
- X-ray window: graphite/Kapton (10 mm width)



\* vacuum (scroll pump,  $\approx 10^{-4}$  bar) and lnert gas atmosphere (e.g. N<sub>2</sub> or user supplied gas mixtures) available

#### monitoring of crystallization of ZnGe<sub>2</sub>O<sub>4</sub>

- in situ XRD measurements performed on Bruker D8 epuipped with Anton Paar HTK1200N
- $2\theta$  range =  $10^{\circ} 80^{\circ}$
- temperature range =  $600 800^{\circ}$ C; 20 K steps; dT/dt  $\approx$  1 K s<sup>-1</sup>; 20 min delay before measurements
- air atmosphere
- phases: ZnGe<sub>2</sub>O<sub>4</sub>, GeO<sub>2</sub> (α-quartz-type)



## in situ temperature-dependent diffraction

#### monitoring of crystallization of ZnGe<sub>2</sub>O<sub>4</sub>



#### grazing incidence diffraction (GIXRD)

- low background energy dispersive SOL-X detector
- sample changer for high throughput
- Bruker EVA for phase analysis
- sample hight cannot be adjusted (necessary for pattern refinement)



#### What can be done?

- qualitative phase analysis (search/match with database)
- single peak fits: lattice parameter (rectangular crystal system) peak witdh (FWHM)

## Instrumentation @ LMC

PANalytical MRD (I.) and MPD (r.) for analysis of thin film and powders, for texture and epitaxy analysis and micro-diffraction



## Instrumentation @ LMC

#### PANalytical MPD (multi purpose diffractometer)

- precise GIXRD measurements of thin films:
  parallel X-ray beam (X-ray mirror and Xe single counter), sample hight can be adjusted (z-scan)
- sample table for x-y scans allows scanning
- reflectivity option for film thickness and roughness
- fast **powder diffraction** with 1-D PIXcel detector

#### What can be done?

- > qualitative phase analysis (search/match with database)
- > quantitative phase analysis (Rietveld refinement with e.g. HIGHSCORE)
- single peak fits: lattice parameter (rectangular crystal system) peak witdh (FWHM)
- structure refinement
  LeBail refinement (lattice parameter)
  Rietveld refinement (all structural parameters)





sputtered  $In_xS_y$  layer T<sub>sub</sub>= 230°C, 340°C, no heating





#### What happened with the sputtered $In_xS_y$ layer?

D. Abou-Ras, G. Kostorz, D. Hariskos, R. Menner, M. Powalla, S. Schorr, A.N. Tiwari, Thin Solid Films 517 (2009) 2792.

## $In_xS_y / CIGSe (T_{sub} = 340^{\circ} C)$

diffusion of Cu and Ga from CIGSe into the buffer  $(In_xS_y) \rightarrow$  formation of vacancy compounds

![](_page_19_Figure_2.jpeg)

## $In_xS_y / CIGSe (T_{sub} = 340^{\circ} C)$

![](_page_20_Figure_1.jpeg)

#### **Ga-gradient in Cu(In,Ga)Se<sub>2</sub> absorber layers**

![](_page_21_Picture_2.jpeg)

ZnO window layer CdS CIGSe absorber Mo back contact glass substrate

cross-sectional SEM image

Ch. A. Kaufmann, R. Caballero, T. Unold, R. Hesse S. Schorr, M. Nichterwitz, H.-W. Schock, Sol. Energy Mat. & Sol. Cells (2008)

## Simulated powder pattern: Cu(In,Ga)Se<sub>2</sub>

#### 112 Bragg peak

![](_page_22_Figure_2.jpeg)

### depth profiles of CIGSe thin films

![](_page_23_Figure_1.jpeg)

#### depth profiles of CIGSe thin films

![](_page_24_Figure_1.jpeg)

## macrostrain and microstrain in thin films

![](_page_25_Figure_1.jpeg)

 $\rightarrow$  shift in peak position reveals stress regime

 $\rightarrow$  separation of size and strain broadening

#### $Cu_2ZnSnS_4$ thin film grown by co-evaporation

![](_page_26_Figure_2.jpeg)

B. A. Schubert, B. Marsen, S. Cinque, T. Unold, R. Klenk, S. Schorr, H.-W. Schock, Progress in Photovolatics: Research and Application (2010)

## microstructure analysis of thin films

- microstructure analysis of CISe thin film absorber layers
- broadening of integral peak breadths β used to deduce microstrain and domain size
- depth-resolved characterization possible by varying incidence angles

Williamson-Hall analysis of CISe using pseudo-Voigt profile function to obtain  $\beta$ (done with Highscore Plus, PANalytical)

![](_page_27_Figure_5.jpeg)

![](_page_27_Figure_6.jpeg)

microstructure analysis of CISe using Thompson-Cox-Hastings pseudo-Voigt profile function to obtain β (done with Fullprof Suite software package)

![](_page_27_Figure_8.jpeg)

→ size and strain directly calculated from corresponding profile parameters

![](_page_28_Picture_0.jpeg)

estimation of thickness, density and roughness of thin films

- X-ray reflectometry is based on varying reflectivities of X-rays when traversing interfaces between dissimilar media (differing optical constants)
- resulting interference fringes allow modeling of thickness, density and roughness of thin layers
- higher contrasts in optical constants (for multi-layer systems) cause stronger oscillations
- layer thickness is inferred by the period of the oscillations

![](_page_28_Figure_7.jpeg)

#### XRR pattern and fitted curve:

#### Results from modeling:

Layer	Layer Description	Density (g/cm3)	Thickness (nm)	Roughness (nm)
2,0	DensityOnly, Fe3O4	5.18	12.845	2.173
1,0	DensityOnly, CoO	6.45	44.143	1.862
Substrate	DensityOnly, SrTiO3	5.1	600000	0.993

## Instrumentation @ LMC

#### PANalytical MRD for texture analysis:

- X-ray lens for high intensive parallel beam
- Eulerian cradle for 3D sample orientation
- Xe single counter
- X'Pert Texture to create pole figures and orientation distribution functions (ODF)

![](_page_29_Picture_6.jpeg)

Pole figures recorded on CuInSe<sub>2</sub> (CISe) chalcopyrite-type thin film absorber layer

![](_page_29_Figure_8.jpeg)

Orientation distribution functions (ODF) shown as contour plot and 3D plot for CISe Bragg peaks 112 and 204

## texture of thin films

hybrid perovskite MAFACsPb $(I_xBr_{1-x})_3$  on glass substrate (C. Rehermann)

![](_page_30_Figure_2.jpeg)

- accidental sample rotation during GIXRD measurement
- "sawtooth" pattern due to highly textured thin film

![](_page_31_Picture_0.jpeg)

## texture of thin films

![](_page_31_Picture_2.jpeg)

110 pole figure @  $2\Theta = 14.0756^{\circ}$ 

 $\rightarrow$  nearly epitaxial thin film

![](_page_31_Picture_5.jpeg)

#### Panalytical MRD for epitaxy analysis and micro-diffraction

![](_page_32_Picture_2.jpeg)

![](_page_32_Picture_3.jpeg)

#### Monocapillary 230 x 0,1

- length 230 mm
- thickness 0,1 mm
- divergence 0,3°

## Instrumentation @ WCRC

#### The 5-axes diffractometer ETA for surface gradient analysis

![](_page_33_Picture_2.jpeg)

- direct sample rotation around the scattering vector
- polycapillary optics and soller + secondary mononchromator for thin film analysis

![](_page_33_Figure_5.jpeg)

#### Principle of residual stress analysis by diffraction methods

![](_page_34_Figure_1.jpeg)

## Instrumentation @ WCRC

#### The energy-dispersive 8-circle diffractometer LEDDI

![](_page_35_Picture_2.jpeg)

Laboratory Energy Dispersive DIffraction

![](_page_35_Figure_4.jpeg)

simultaneous data acquisition with two detectors

![](_page_35_Figure_6.jpeg)

 $\theta_1 = \theta_2$ ;  $\chi = 60^\circ$ 

ω

in- and out-of-plane residual stress depth profiles from a single  $\chi$ -scan

#### Full support : Planning and conducting experiments & data evaluation

#### Stahl\_sin2psi\_Probe\_4\_1.psi / Linie 1 **EDDI-LEDDI** 0.2022 Ein MATHEMATICA®-Progammsystem zur energiedispersiven 0.202 Eigenspannungsanalyse 0.201 Notebookdatei EDDI-LEDDI.nb 0.2015 EDDIbasicLEDDI.m Packagedatei: Letzte Änderung: 24. August 2016 0.20125 Listen mit diffraktionselastischen Konstanten (DEK) . 0.201 **Texture analysis** EDDI \* 111 0.20075 0.2 0.4 0.6 0.8 • 221 1 111 A .... Radioaktives Präparat **Residual stress** Detektor im Labor ..... A 422 Nützliche Tools \* 110/ 111 Vorbereitung von ED-Messungen an EDDI analysis \* 313 Auswertung von ED-Beugungsspektrei 60 r (µm) 100 120 4 220 20 Linienlagenkorrekturer 1 11 A 10 Darstellung von Ergebnissen 320/4 Quantitative Phasenanalyse zweiphasiger Gefüge Texturmessungen Ermittlung von Eigenspannungen und Eigenspannunstiefenverteilungen 20 40 z, r (ym) 60 80 1000 0 Ted Ted Ties Innert 🔜 fx 😪 📑 📄 🖳 🔄 Run Secto -1000 a, = -8422.99 ± 47.16 012 a, = 5500.97 ± 47.07 △ 104 -2000 $\sigma(z)^{Rietveld}$ a, = 0.8268 ± 0.0148 110 clear all -3000 σ<sub>II</sub> (MPa) Preparation of data evaluation -4000 3000 $\dot{\sigma}(\tau)^{Rietveld}$ measured profile calculated profile residual -5000 2500 -6000 -7000 2000 -8000 [cts/s] 1500 -9000 ŝ 10 15 0 5 1000 500

Fit results

50 NO 00

are an an

- 10

**RIETVELD** analysis

(stress, microstructure)

linfo = T.Materia

.Material.Name = P.MPDFileName:

T.Substrate = Sample.Substrate() if (P.ShowSubstratePeaks)

\* Default value for maximum T.Material.EnergyMax = 100;

energy

SubstratePeaks = P.ShowSubstratePeaks;

LoadFromMpdFile(P.MPDFileName)

Script based

evaluation

program

37

60

20

30

40

Energy [keV]

(b)

б

## Synchrotron-like conditions in the lab?

![](_page_37_Figure_1.jpeg)

Ga-Kα: 9.2 keV

In-Kα: 24.2 keV

#### WCRC/EMIL: 160 kV source

![](_page_37_Picture_5.jpeg)

## LMC: 70 kV source

![](_page_37_Picture_7.jpeg)

#### in situ EDXRD/XRF during thin film growth

#### Energy-dispersive X-ray diffraction and fluorescence (EDXRD/XRF)

![](_page_38_Figure_2.jpeg)

H. Rodriguez-Alvarez, A. Weber, J. Lauche, C. A. Kaufmann, T. Rissom, D. Greiner, M. Klaus, T. Unold, C. Genzel, H.-W. Schock, R. Mainz. Advanced Energy Materials **3**, 1381-1387 (2013).

#### Planar defects in Cu(In,Ga)Se<sub>2</sub> create a diffraction signal

#### without Cu-rich stage

![](_page_39_Picture_2.jpeg)

with Cu-rich stage

![](_page_39_Picture_4.jpeg)

![](_page_39_Figure_5.jpeg)

R. Mainz et al., Energy Environ. Sci. 9, 1818 (2016)

#### Monitoring PD annihilation by real-time XRD

#### without Cu-rich stage

![](_page_40_Picture_2.jpeg)

![](_page_40_Picture_3.jpeg)

with Cu-rich stage

![](_page_40_Figure_4.jpeg)

R. Mainz et al., Energy Environ. Sci. 9, 1818 (2016)

## Cu<sub>2</sub>ZnSnS<sub>4</sub> film formation from wurtzite nanorods

![](_page_41_Picture_2.jpeg)

# From nanorods to large grains within a few seconds!

- $\rightarrow$  correlation of phase formation and domain growth
  - $\rightarrow$  phase-transition-driven grain growth

![](_page_41_Figure_6.jpeg)

new in situ X-ray laboratory

![](_page_42_Figure_1.jpeg)

![](_page_43_Picture_0.jpeg)

New X-ray diffractometer for powder diffraction and GIXRD was ordered for WCRC!

![](_page_43_Picture_2.jpeg)

course on X-ray diffraction (for PhD students) will be organized next year (June 2018) @LMC

Scientists from all HZB divisions as well as external users have access to the X-Ray CoreLab.

1st step  $\rightarrow$  each potential user has to register online the user has to declare to follow the lab rules

2nd step → booking an instrument of the CoreLab via the online calendar system user should give a short description of the planned experiment and the samples he/she wants to study

3rd step  $\rightarrow$  check by the scientific lab manager to make sure, that the user has chosen the suitable instrument for his/her problem

4th step → scientific lab manager confirms the booking and the user gets access to the X-Ray CoreLab

LMC  $\rightarrow$  after introduction by the lab manager the user can do the experiments WCRC  $\rightarrow$  user experiments supported by instrument experts

![](_page_45_Picture_0.jpeg)

## Welcome to the X-Ray CoreLab!

Thank you for your attention!